

A COMPOUND SEMICONDUCTOR SUBSTRATE, A PELLICLE FILM, AND A
METHOD FOR MANUFACTURING A COMPOUND SEMICONDUCTOR
SUBSTRATE

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ABSTRACT OF THE DISCLOSURE

A compound semiconductor substrate, a pellicle film, and a method for
manufacturing a compound semiconductor substrate that can achieve thinning of SiC film
10 are provided.

A method for manufacturing a compound semiconductor substrate comprises: a
step of forming a SiC film on obverse side of a Si substrate, and a step of exposing at least
part of the reverse side of the SiC film by wet etching. In the step of exposing at least part
of the reverse side of the SiC film, at least the Si substrate and the SiC film are moved
15 with respect to liquid chemical used for the wet etching.

[Fig. 1]